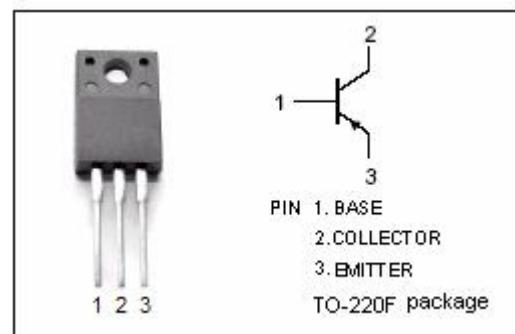


isc Silicon PNP Power Transistor

2SA1744

DESCRIPTION

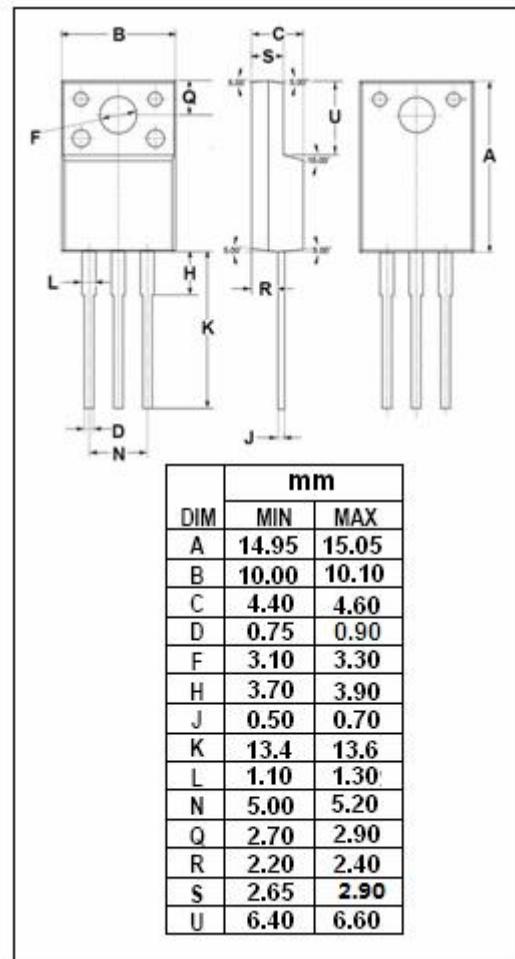
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = -60V$ (Min)
- High DC Current Gain-
: $h_{FE} = 100$ (Min)@ ($V_{CE} = -2V$, $I_C = -3A$)
- Low Saturation Voltage-
: $V_{CE(sat)} = -0.3V$ (Max)@ ($I_C = -8A$, $I_B = -0.4A$)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for use as a driver in DC/DC converters and actuators.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7.0	V
I_C	Collector Current-Continuous	-15	A
I_{CM}	Collector Current-Pulse	-30	A
I_B	Base Current-Continuous	-7.5	A
P_T	Total Power Dissipation @ $T_C=25^\circ C$	30	W
	Total Power Dissipation @ $T_a=25^\circ C$	2.0	
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~150	°C



isc Silicon PNP Power Transistor**2SA1744****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _c =-10mA, I _b =0	-60	--	--	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -60V; I _e = 0	--	--	-10	μA
I _{CEO}	Collector Cutoff Current	V _{CE} = -60V; I _b =0	--	--	-1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _c = 0	--	--	-10	μA
h _{FE-1*}	DC Current Gain	I _c = -1.5A; V _{CE} = -2V	100	--	--	
h _{FE-2*}	DC Current Gain	I _c = -3A; V _{CE} = -2V	100	--	400	
h _{FE-3*}	DC Current Gain	I _c = -8A; V _{CE} = -2V	60	--	--	
V _{CE(sat)-1*}	Collector-Emitter Saturation Voltage	I _c = -8A; I _b = -0.4A	--	--	-0.3	V
V _{CE(sat)-2*}	Collector-Emitter Saturation Voltage	I _c = -12A; I _b = -0.6A	--	--	-0.5	V
V _{BE(sat)-1*}	Base-Emitter Saturation Voltage	I _c = -8A; I _b = -0.4A	--	--	-1.2	V
V _{BE(sat)-2*}	Base-Emitter Saturation Voltage	I _c = -12A; I _b = -0.6A	--	--	-1.5	V
C _{OB}	Output Capacitance	I _e = 0; V _{CB} = -10V; f= 1MHz	--	290	--	pF
f _T	Current-Gain—Bandwidth Product	I _c = -1.5A ; V _{CE} = -10V	--	80	--	MHz

* Pulse test PW ≤ 350 μs, duty cycle ≤ 2%

h_{FE} CLASSIFICATION

Marking	M	L	K
h _{FE-2*}	100-200	150-300	200-400

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